TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type (U-MOS III)

# **TPCP8101**

#### Notebook PC Applications Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON-resistance:  $R_{DS}$  (ON) = 24 m $\Omega$  (typ.)

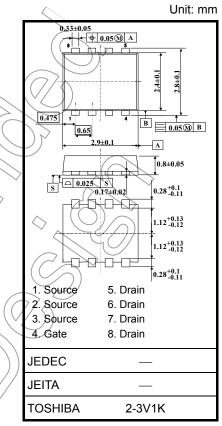
$$(V_{\rm GS} = -4.5 \text{ V})$$

- High forward transfer admittance:  $|\,Y_{\rm fs}\,|$  = 14 S (typ.)
- Low leakage current:  $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -20 \ V)$
- Enhancement model:  $V_{th} = -0.5$  to -1.2 V

 $(V_{DS} = -10 \text{ V}, \text{ I}_{D} = -200 \text{ }\mu\text{A})$ 

#### Absolute Maximum Ratings (Ta = 25°C)

					$ /// \wedge$
Characteristic		Symbol	Rating	Unit	
Drain-source voltage			V <sub>DSS</sub>	-20	y
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )			V <sub>DGR</sub>	~20	> v
Gate-source voltage			V <sub>GSS</sub>	<u>+8</u>	V
Drain current	DC (N	Note 1)	ID	-5.6	A
	Pulse (N	Note 1)	I <sub>DP</sub>	-22,4	A
Drain power dissipation (t = 5 s) (Note 2a)			Pp	1.68	×
Drain power dissipation (t = 5 s) (Note 2b)			PD	0.84	w
Single-pulse avalanche energy(Note 3)			EAS	20.3	Lm
Avalanche current			IAR	-5.6	A
Repetitive avalanche energy (Note 4)			∕J¢AR	0.168	⊃mJ
Channel temperature			T <sub>ch</sub>	(150/))	°C
Storage temperature range			T <sub>stg</sub>	-55 to 150	°C



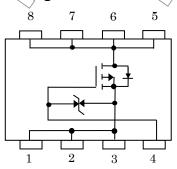
Weight: 0.017 g (typ.)

Note: For Notes 1 to 5, refer to the next page.

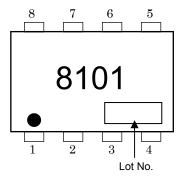
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

This transistor is an electrostatic-sensitive device. Handle with care.

#### **Circuit Configuration**



#### Marking (Note 5)

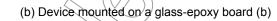


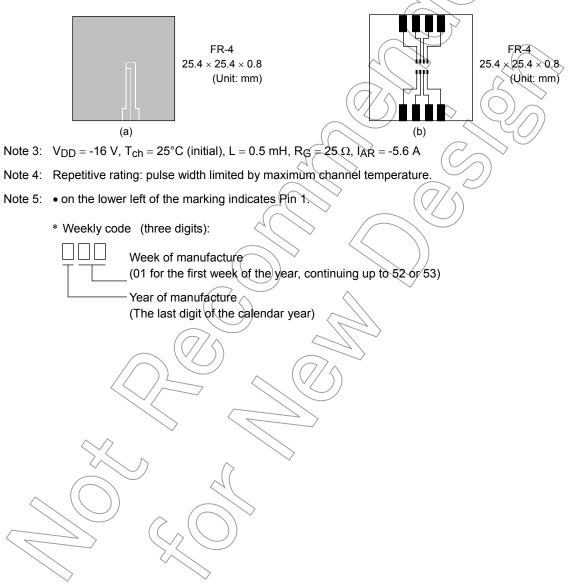
#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient $(t = 5 s)$ (Note 2a)	R <sub>th (ch-a)</sub>	74.4	°C/W
Thermal resistance, channel to ambient (t = 5 s) (Note 2b)	R <sub>th (ch-a)</sub>	148.8	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C during use of the device.

Note 2: (a) Device mounted on a glass-epoxy board (a)





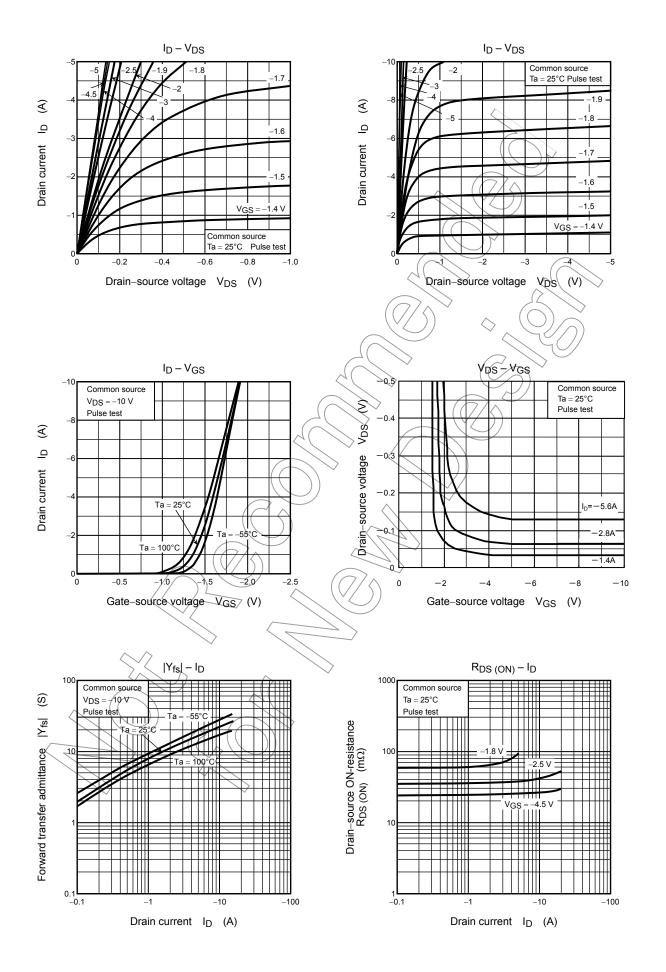
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Тур.	Мах	Unit
Gate leakage cu	rrent	I <sub>GSS</sub>	$V_{GS}=\pm 8~V,~V_{DS}=0~V$	_	_	±10	μA
Drain cutoff curre	ent	I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	—	-10	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D$ = -10 mA, $V_{GS}$ = 0 V	-20	—		V
		V (BR) DSX	$I_D = -10 \text{ mA}, V_{GS} = 8 \text{ V}$	-12			
Gate threshold v	oltage	V <sub>th</sub>	$V_{DS}=\text{-10 V},\ I_{D}=\text{-200 }\mu\text{A}$	-0.5		-1.2	V
Drain-source ON-resistance			$V_{GS} = -1.8 \text{ V}, \text{ I}_{D} = -1.4 \text{ A}$		67	90	mΩ
		R <sub>DS (ON)</sub>	$V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -2.8 \text{ A}$	$\mathcal{A}$	36	41	
			$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -2.8 \text{ A}$		24	30	
Forward transfer admittance		Y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -2.8 A	7	14		S
Input capacitance		C <sub>iss</sub>		_	1550		
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = -10 V, V_{GS} = 0 V, f = 1 MHz$		215	$\searrow$	pF
Output capacitance		C <sub>oss</sub>	$(\overline{\gamma})^{\sim}$	-6	265	> —	
Switching time	Rise time	tr	V <sub>GS</sub> 0 V - L <sub>D</sub> = -2.8 A	K	KO)	) _	
	Turn-on time	t <sub>on</sub>			> <u>)</u> 13	_	
	Fall time	tf		Z	21		ns
	Turn-off time	toff	$V_{DD} \approx -10 \text{ V}$ Duty $\leq 1\%$ , t <sub>W</sub> $\neq 10  \mu\text{s}$		68	_	
Total gate charge (gate-source plus gate-drain)		Qg	V <sub>DD</sub> ≈ -16 V, V <sub>GS</sub> = -5 V,		19		
Gate-source charge		Qgs	$I_{\rm D} = -5.6  {\rm A}$		14		nC
Gate-drain ("Mille	er") charge	Qgq			5		

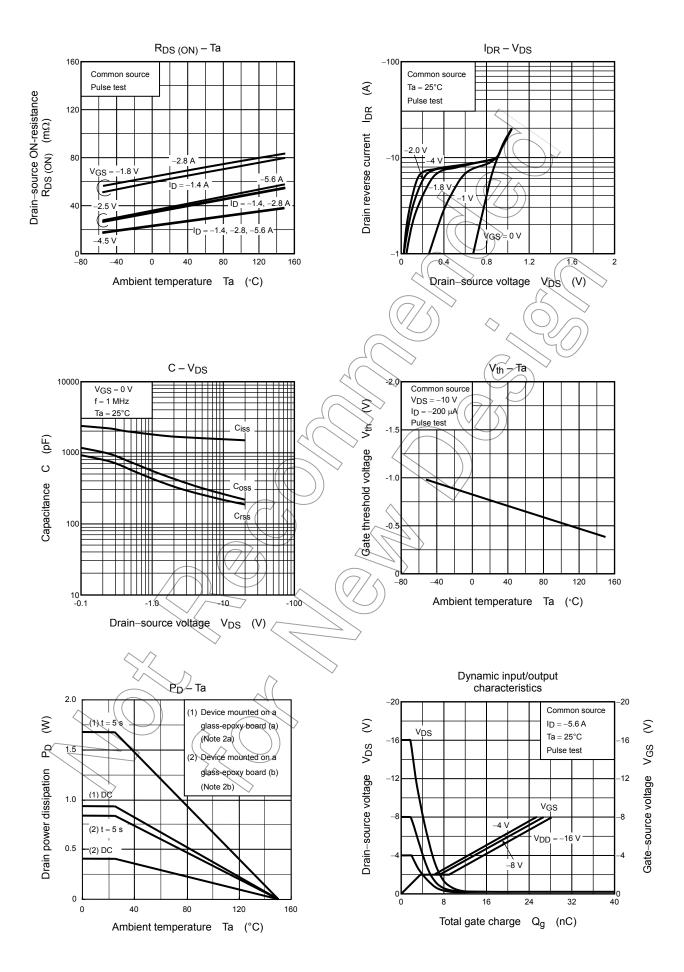
# Source-Drain Ratings and Characteristics (Ta = 25°C)

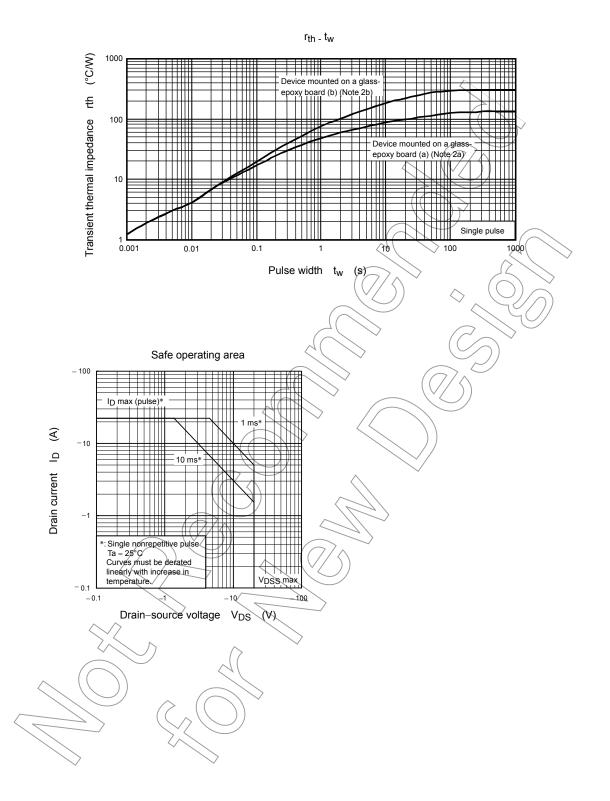
Charac	teristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)		-	_	_	-22.4	А
Forward voltage	(diode)	V <sub>DSF</sub>	$I_{DR} = -5.6A, V_{GS} = 0 V$	_	_	1.2	V

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